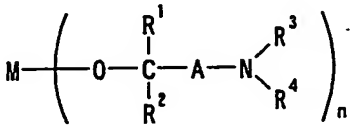
WHAT IS CLAIMED IS:

1. A metal compound represented by general formula (I):



(I)

wherein R^1, R^2, R^3, and R^4 each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a lead atom, a titanium atom or a zirconium atom; n represents 2 when M is a lead atom or 4 when M is a titanium or zirconium atom.

2. The metal compound according to claim 1, wherein A is a methylene group.

3. The metal compound according to claim 1 or 2, wherein M is a lead atom.

4. The metal compound according to claim 1 or 2, wherein M is a titanium atom.

5. The metal compound according to claim 1 or 2, wherein M is a zirconium atom.

6. A material for thin film formation comprising the metal compound according to any one of claims 1 to 5.

7. A material for thin film formation comprising the metal compound of claim 3, the metal compound of claim 4, and the metal compound of claim 5.

8. A material for thin film formation comprising the metal compound of claim 3, tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium.

9. A process for thin film formation comprising vaporizing the material for thin film formation according to claim 6, 7 or 8, introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

10. A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing the metal compound of claim 4, and a material for thin film formation containing the metal compound of claim 5 to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

11. A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

12. A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing tetra(tert-butoxy)titanium, and a material for thin film formation containing tetra(tert-butoxy)zirconium to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.